

**Picoampere diode**

**BAV45**

**FEATURES**

- Extremely low leakage current: max. 5 pA
- Low diode capacitance
- Light insensitive.

**APPLICATION**

- Clamping
- Holding
- Peak follower
- Time delay circuits
- Logarithmic amplifiers
- Protection of insulated gate field-effect transistors.

**DESCRIPTION**

Silicon diode in a metal TO-18 can. It has an extremely low leakage current over a wide temperature range combined with a low capacitance and is not sensitive to light.

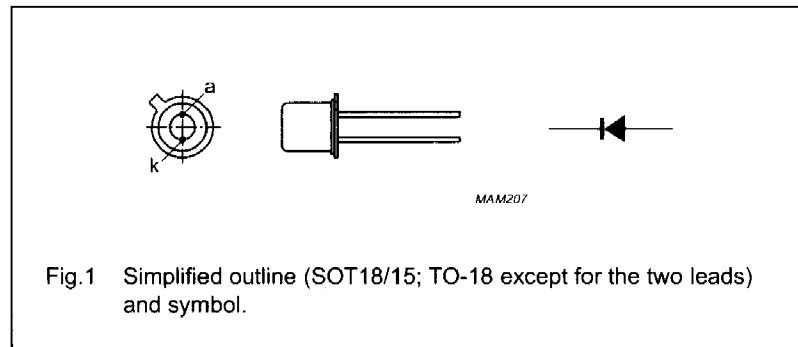


Fig.1 Simplified outline (SOT18/15; TO-18 except for the two leads) and symbol.

**CAUTION**

Handle the device with care whilst soldering into the circuit. The extremely low leakage current can only be guaranteed when the bottom is free from solder flux or other contaminations.

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage		-	35	V
$V_R$	continuous reverse voltage		-	20	V
$I_F$	continuous forward current	see Fig.2	-	50	mA
$I_{FRM}$	repetitive peak forward current		-	100	mA
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ }^\circ\text{C}$ ; note 1	-	200	mW
$T_{stg}$	storage temperature		-65	+125	$^\circ\text{C}$
$T_j$	junction temperature		-	125	$^\circ\text{C}$

**Note**

1. Device mounted on a FR4 printed-circuit board.



**ELECTRICAL CHARACTERISTICS**

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$V_F$	forward voltage	$I_F = 10\text{ mA}$ ; see Figs 3 and 4	1	V
$I_R$	reverse current	see Fig.5 $V_R = 5\text{ V}$ $V_R = 5\text{ V}; T_j = 80\text{ }^\circ\text{C}$ $V_R = 20\text{ V}$	5 250 10	$\mu\text{A}$ $\mu\text{A}$ $\mu\text{A}$
$C_d$	diode capacitance	$f = 1\text{ MHz}; V_R = 0$ ; see Fig.6	1.3	$\mu\text{F}$
$t_{rr}$	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$ ; $R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$ ; see Fig.7	600	ns

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient; note 1	500	K/W

**Note**

1. Device mounted on a FR4 printed-circuit board.

**PACKAGE OUTLINE**

